



STH210N75F6-2

N-channel 75 V, 2.7 mΩ typ., 180 A STripFET™ VI DeepGATE™ Power MOSFET in H²PAK-2 package

Datasheet — production data

Features

| Order code | V _{DSS} | R _{DS(on)} max | I _D |
|---------------|------------------|-------------------------|----------------|
| STH210N75F6-2 | 75 V | < 3.4 mΩ | 180 A |

- Low gate charge
- Very low on-resistance
- High avalanche ruggedness

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the 6th generation of STripFET™ DeepGATE™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest R_{DS(on)} in all packages.

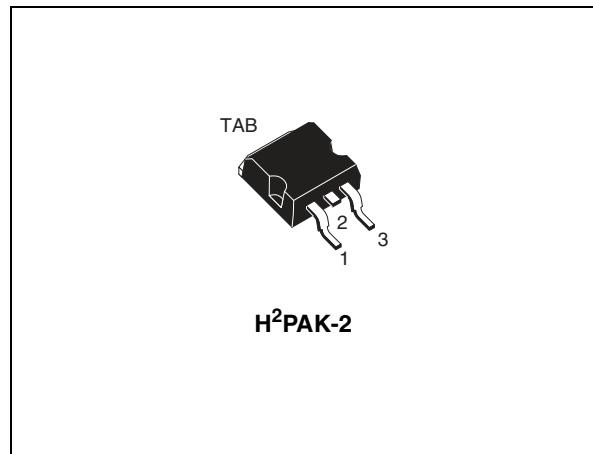


Figure 1. Internal schematic diagram

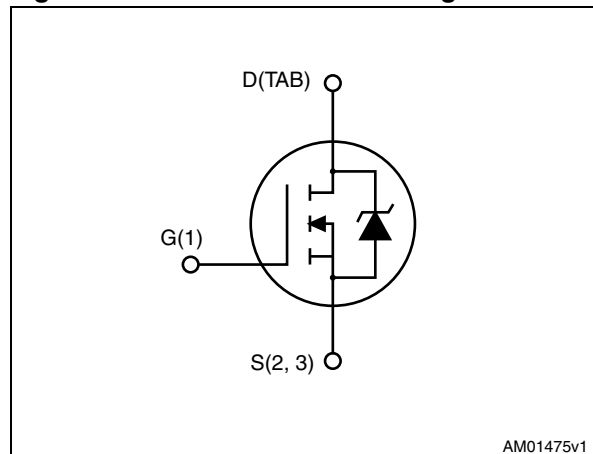


Table 1. Device summary

| Order code | Marking | Package | Packaging |
|---------------|----------|----------------------|---------------|
| STH210N75F6-2 | 210N75F6 | H ² PAK-2 | Tape and reel |

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1 Electrical ratings

Table 2. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|----------------|-----------------------------------------------------------------|-------------|---------------------|
| V_{DS} | Drain-source voltage | 75 | V |
| V_{GS} | Gate-source voltage | ± 20 | V |
| I_D | Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$ | 180 | A |
| I_D | Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$ | 150 | A |
| $I_{DM}^{(1)}$ | Drain current (pulsed) | 720 | A |
| P_{TOT} | Total dissipation at $T_C = 25\text{ }^\circ\text{C}$ | 300 | W |
| $E_{AS}^{(2)}$ | Single pulse avalanche energy | 540 | mJ |
| | Derating factor | 2 | W/ $^\circ\text{C}$ |
| T_{stg} | Storage temperature | - 55 to 175 | $^\circ\text{C}$ |
| T_j | Operating junction temperature | | |

1. Current limited by package.
2. Starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = 60\text{ A}$, $V_{DD} = 50\text{ V}$.

Table 3. Thermal data

| Symbol | Parameter | Value | Unit |
|---------------------|--------------------------------------|-------|---------------------------|
| $R_{thj-case}$ | Thermal resistance junction-case max | 0.5 | $^\circ\text{C}/\text{W}$ |
| $R_{thj-pcb}^{(1)}$ | Thermal resistance junction-pcb max | 35 | $^\circ\text{C}/\text{W}$ |

1. When mounted on FR-4 board of 1 inch², 2 oz Cu.

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. On/off states

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|--------------------------------------------------|-----------------------------------------------------------------------|------|------|-----------|--------------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage ($V_{GS} = 0$) | $I_D = 250\ \mu A$ | 75 | | | V |
| I_{DSS} | Zero gate voltage drain current ($V_{GS} = 0$) | $V_{DS} = 75\text{ V}$ $V_{DS} = 75\text{ V}, T_C = 125\text{ °C}$ | | | 1 100 | μA μA |
| I_{GSS} | Gate-body leakage current ($V_{DS} = 0$) | $V_{GS} = \pm 20\text{ V}$ | | | ± 100 | nA |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{DS} = V_{GS}, I_D = 250\ \mu A$ | 2 | | 4 | V |
| $R_{DS(on)}$ | Static drain-source on-resistance | $V_{GS} = 10\text{ V}, I_D = 90\text{ A}$ | | 2.7 | 3.4 | m Ω |

Table 5. Dynamic

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------|------------------------------|---------------------------------------------------------------------------------------------------|------|-------|------|------|
| C_{iss} | Input capacitance | | | 11800 | | pF |
| C_{oss} | Output capacitance | $V_{DS} = 25\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0$ | - | 1060 | - | pF |
| C_{rss} | Reverse transfer capacitance | | | 394 | | pF |
| Q_g | Total gate charge | $V_{DD} = 37.5\text{ V}, I_D = 120\text{ A},$ $V_{GS} = 10\text{ V}$ <i>(see Figure 14)</i> | | 171 | | nC |
| Q_{gs} | Gate-source charge | | - | 50 | - | nC |
| Q_{gd} | Gate-drain charge | | | 36 | | nC |

Table 6. Switching times

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|--------------|---------------------|------------------------------------------------------------------------------------------------------------------|------|------|------|------|
| $t_{d(on)}$ | Turn-on delay time | $V_{DD} = 40\text{ V}, I_D = 60\text{ A}$ $R_G = 4.7\ \Omega, V_{GS} = 10\text{ V}$ <i>(see Figure 13)</i> | - | 34 | - | ns |
| t_r | Rise time | | - | 70 | - | ns |
| $t_{d(off)}$ | Turn-off-delay time | $V_{DD} = 40\text{ V}, I_D = 60\text{ A}$ $R_G = 4.7\ \Omega, V_{GS} = 10\text{ V}$ <i>(see Figure 13)</i> | - | 154 | - | ns |
| t_f | Fall time | | - | 71 | - | ns |

Table 7. Source drain diode

| Symbol | Parameter | Test conditions | Min. | Typ. | Max | Unit |
|-----------------------------------|------------------------------------------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------|------|------------------|-----|---------------|
| I_{SD} | Source-drain current | | - | | 180 | A |
| $I_{SDM}^{(1)}$ | Source-drain current (pulsed) | | - | | 720 | A |
| $V_{SD}^{(2)}$ | Forward on voltage | $I_{SD} = 180 \text{ A}, V_{GS} = 0$ | - | | 1.5 | V |
| t_{rr} Q_{rr} I_{RRM} | Reverse recovery time Reverse recovery charge Reverse recovery current | $I_{SD} = 120 \text{ A}, V_{DD} = 60 \text{ V}$ $di/dt = 100 \text{ A}/\mu\text{s}$, $T_j = 150 \text{ }^\circ\text{C}$ <i>(see Figure 15)</i> | - | 60 144 4.8 | | ns nC A |

1. Current limited by package.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

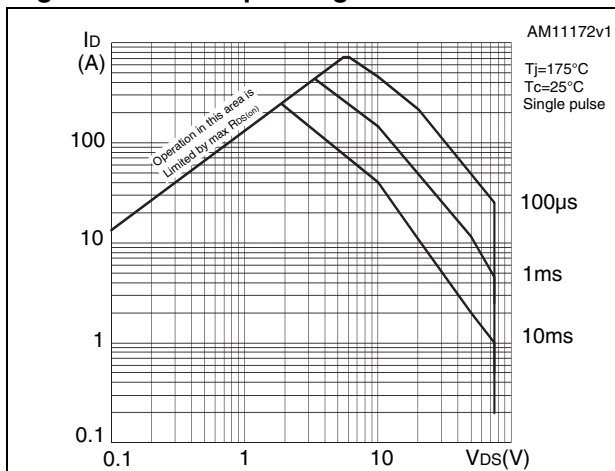


Figure 3. Thermal impedance

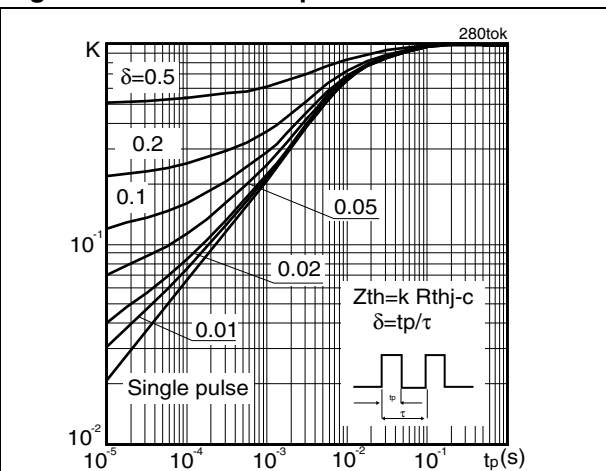


Figure 4. Output characteristics

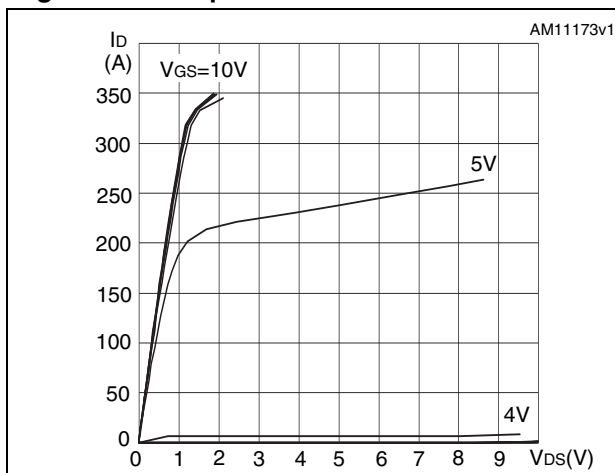


Figure 5. Transfer characteristics

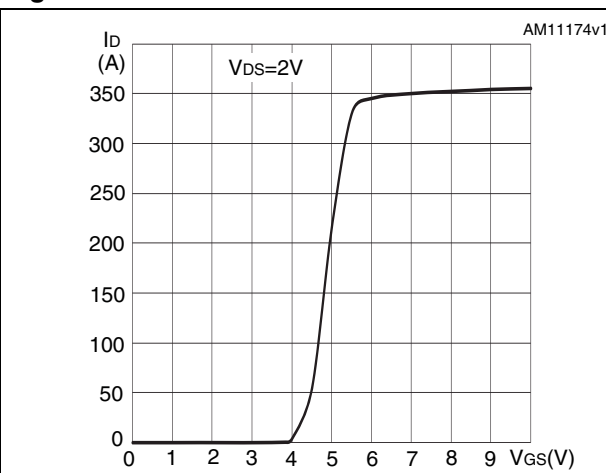


Figure 6. Normalized V_{DS} vs temperature

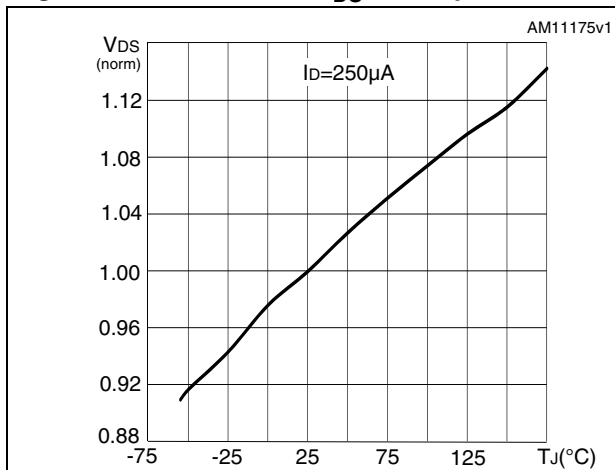


Figure 7. Static drain-source on-resistance

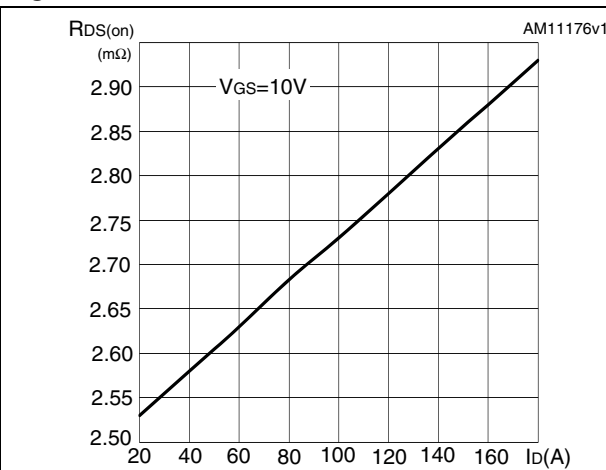


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

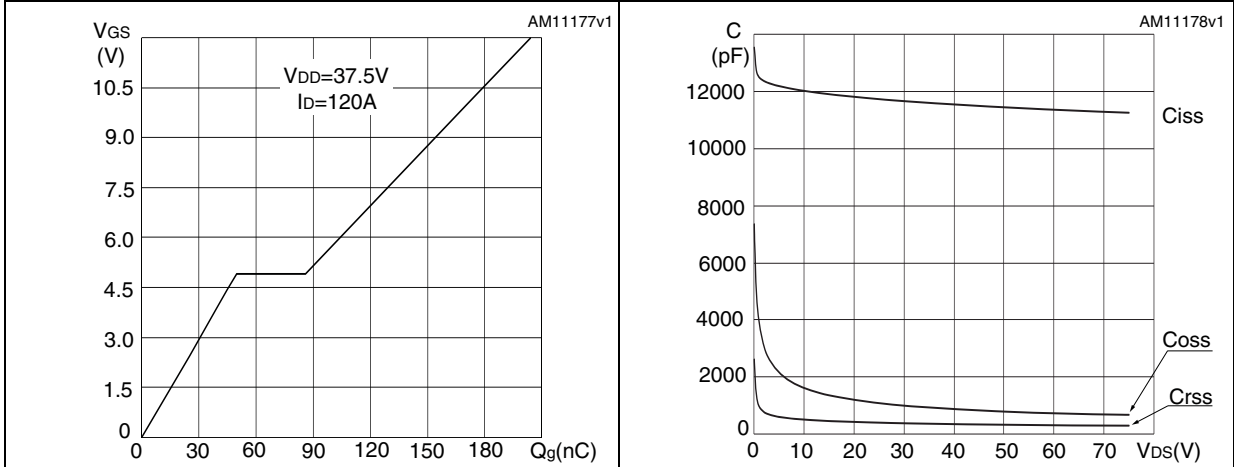


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on-resistance vs temperature

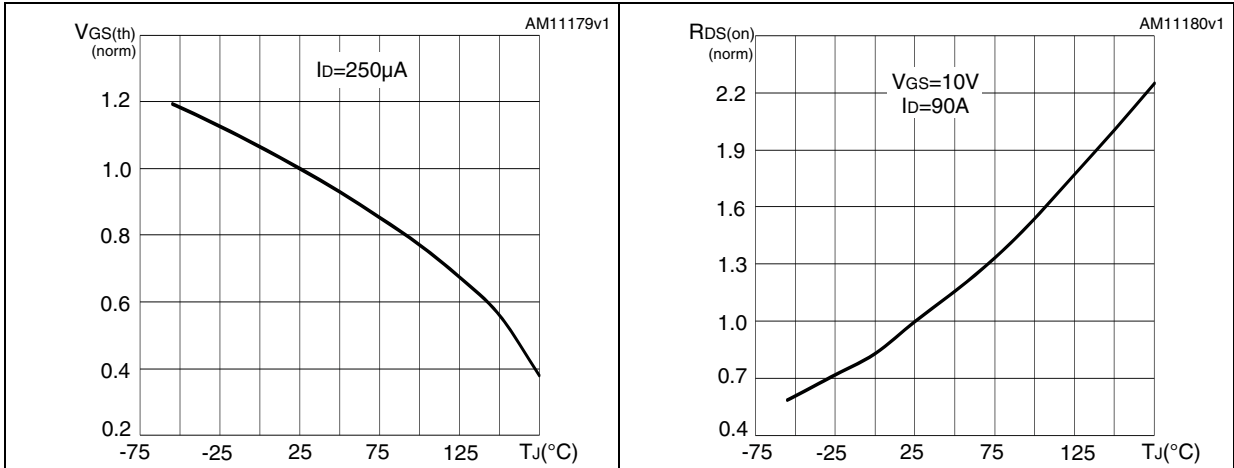
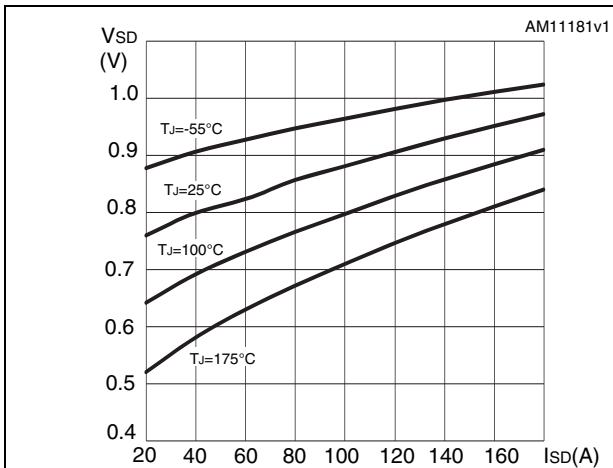


Figure 12. Source-drain diode forward characteristics



3 Test circuits

Figure 13. Switching times test circuit for resistive load

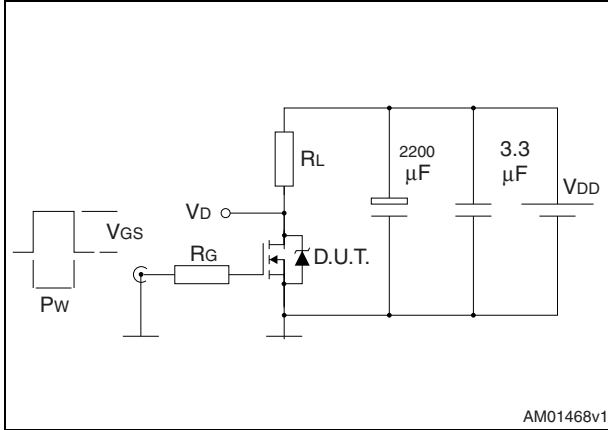


Figure 14. Gate charge test circuit

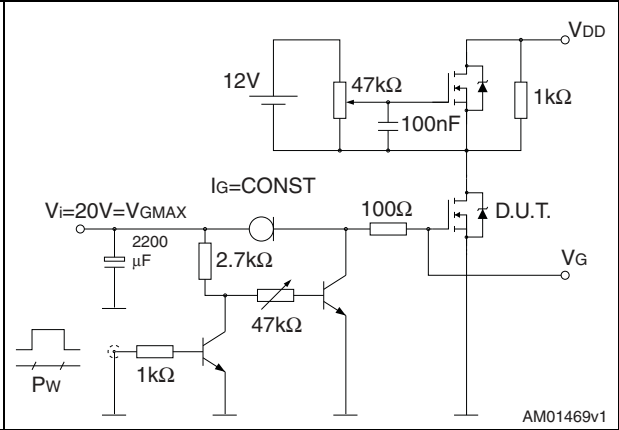


Figure 15. Test circuit for inductive load switching and diode recovery times

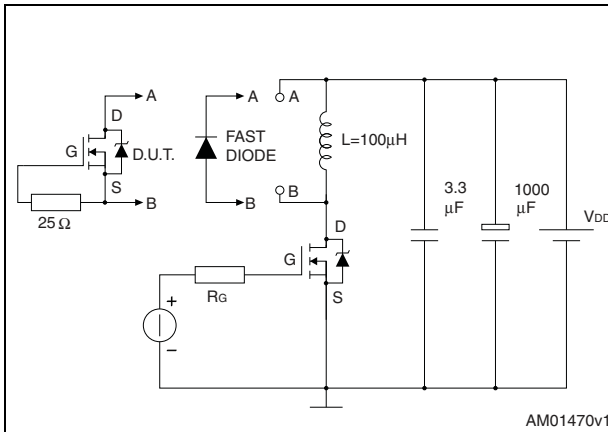


Figure 16. Unclamped inductive load test circuit

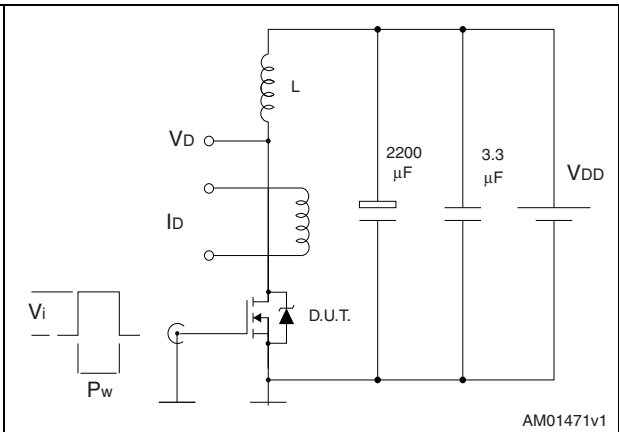


Figure 17. Unclamped inductive waveform

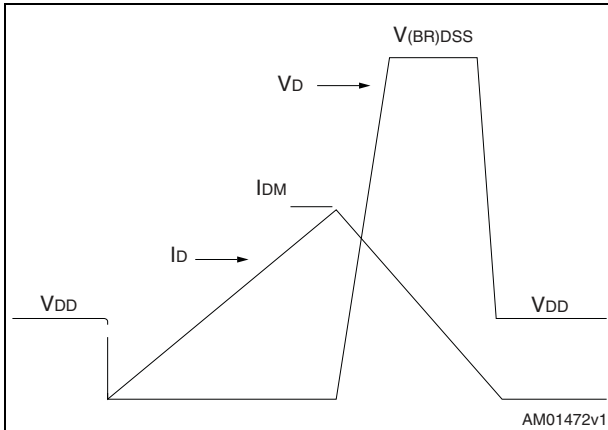
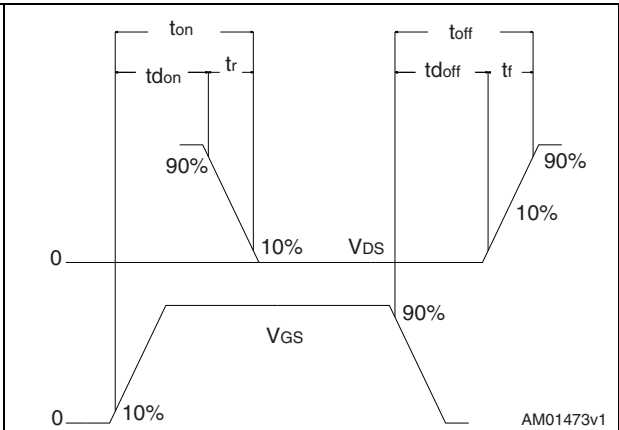


Figure 18. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 8. H²PAK-2 mechanical data

| Dim. | mm | | |
|------|-------|------|-------|
| | Min. | Typ. | Max. |
| A | 4.30 | | 4.80 |
| A1 | 0.03 | | 0.20 |
| C | 1.17 | | 1.37 |
| e | 4.98 | | 5.18 |
| E | 0.50 | | 0.90 |
| F | 0.78 | | 0.85 |
| H | 10.00 | | 10.40 |
| H1 | 7.40 | | 7.80 |
| L | 15.30 | | 15.80 |
| L1 | 1.27 | | 1.40 |
| L2 | 4.93 | | 5.23 |
| L3 | 6.85 | | 7.25 |
| L4 | 1.5 | | 1.7 |
| M | 2.6 | | 2.9 |
| R | 0.20 | | 0.60 |
| V | 0° | | 8° |

Figure 19. H²PAK-2 drawing

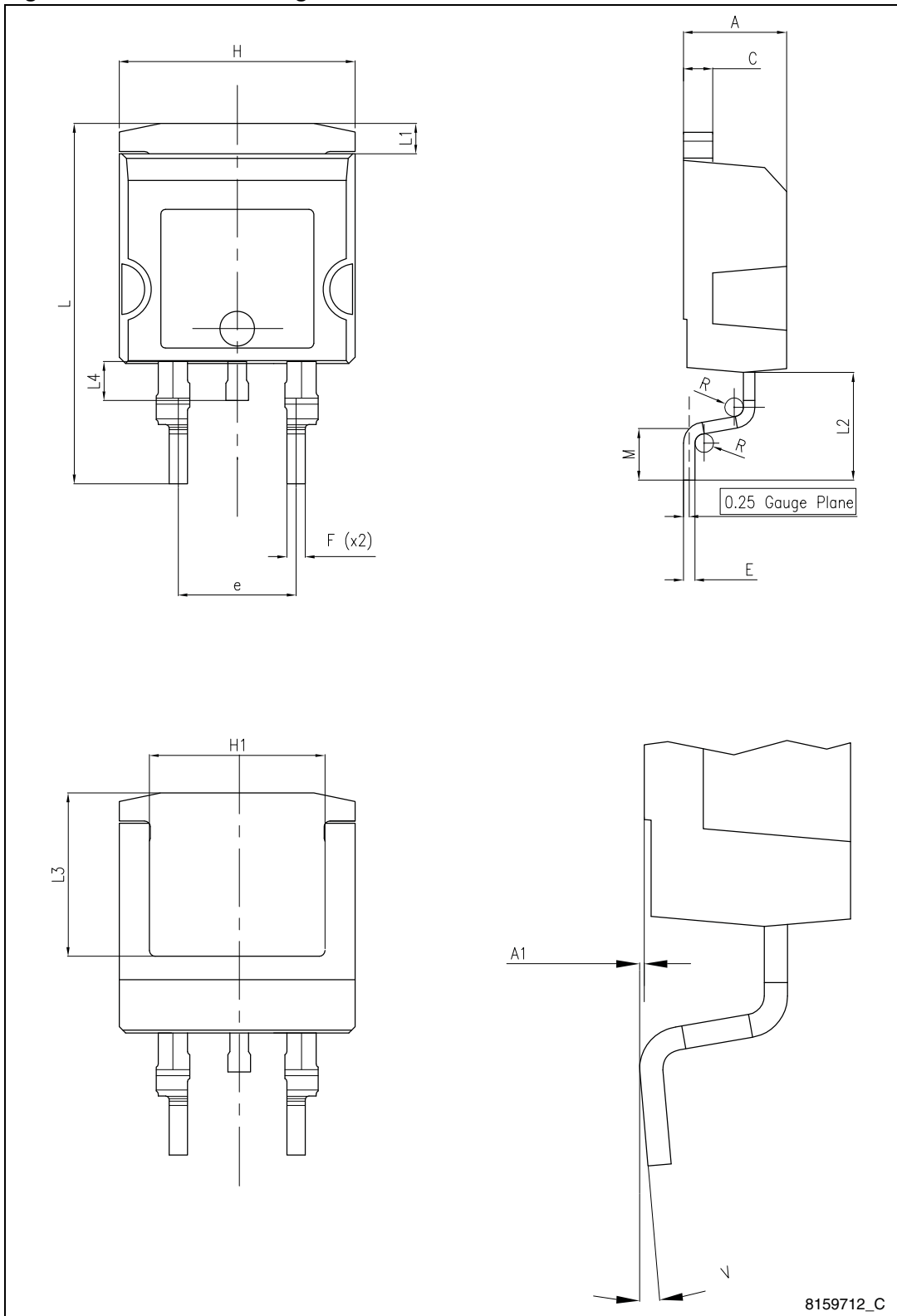
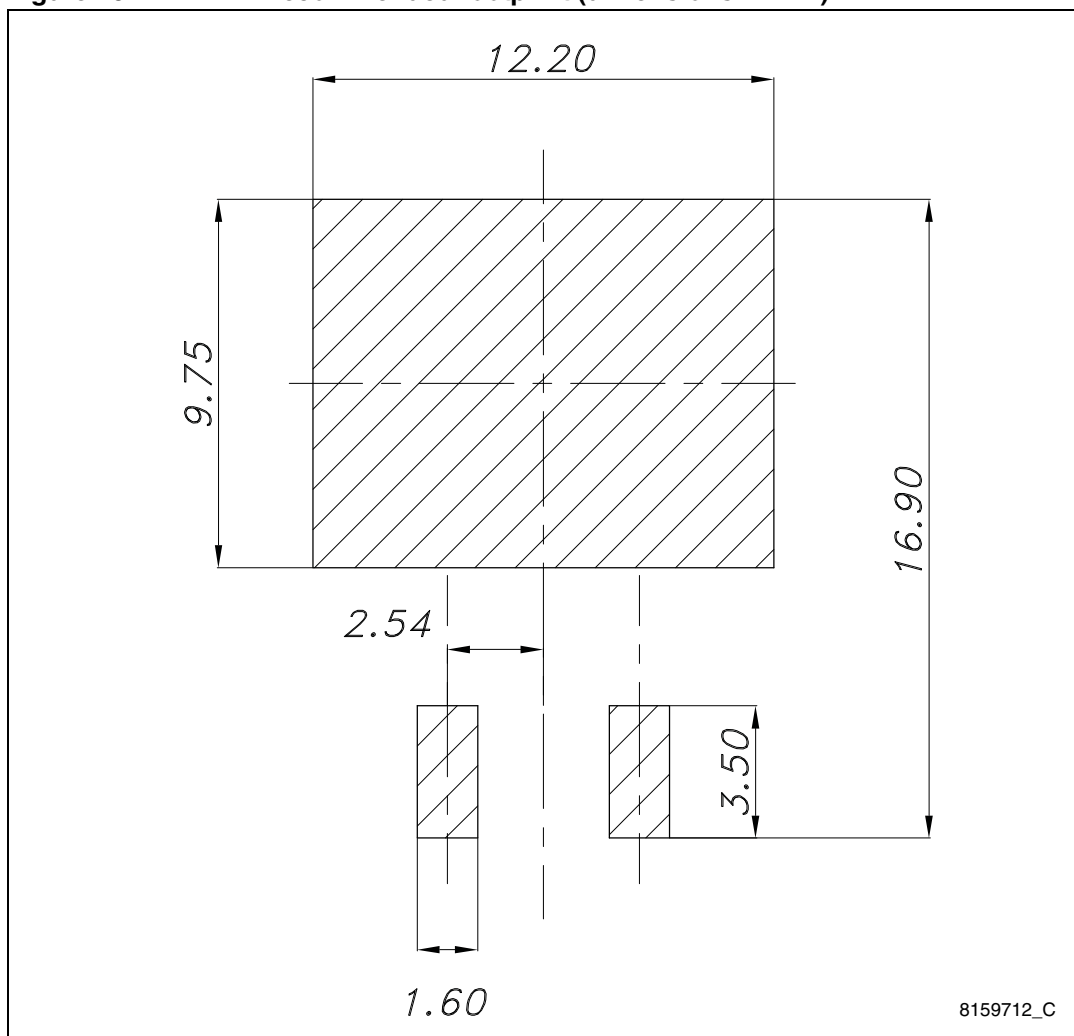


Figure 20. H²PAK-2 recommended footprint (dimensions in mm)



8159712_C

5 Packaging mechanical data

Table 9. H²PAK-2 tape and reel mechanical data

| Tape | | | Reel | | |
|------|------|------|----------|------|------|
| Dim. | mm | | Dim. | mm | |
| | Min. | Max. | | Min. | Max. |
| A0 | 10.5 | 10.7 | A | | 330 |
| B0 | 15.7 | 15.9 | B | 1.5 | |
| D | 1.5 | 1.6 | C | 12.8 | 13.2 |
| D1 | 1.59 | 1.61 | D | 20.2 | |
| E | 1.65 | 1.85 | G | 24.4 | 26.4 |
| F | 11.4 | 11.6 | N | 100 | |
| K0 | 4.8 | 5.0 | T | | 30.4 |
| P0 | 3.9 | 4.1 | | | |
| P1 | 11.9 | 12.1 | Base qty | | 1000 |
| P2 | 1.9 | 2.1 | Bulk qty | | 1000 |
| R | 50 | | | | |
| T | 0.25 | 0.35 | | | |
| W | 23.7 | 24.3 | | | |

Figure 21. Tape

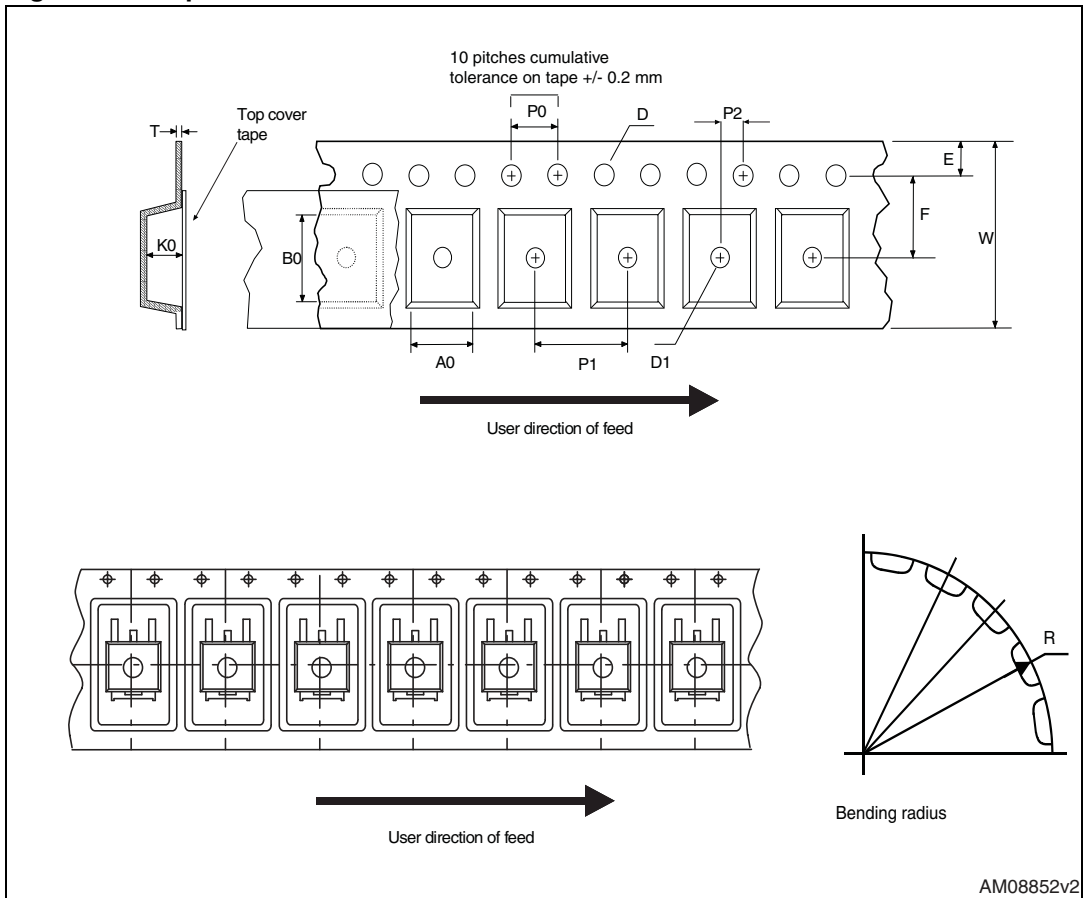
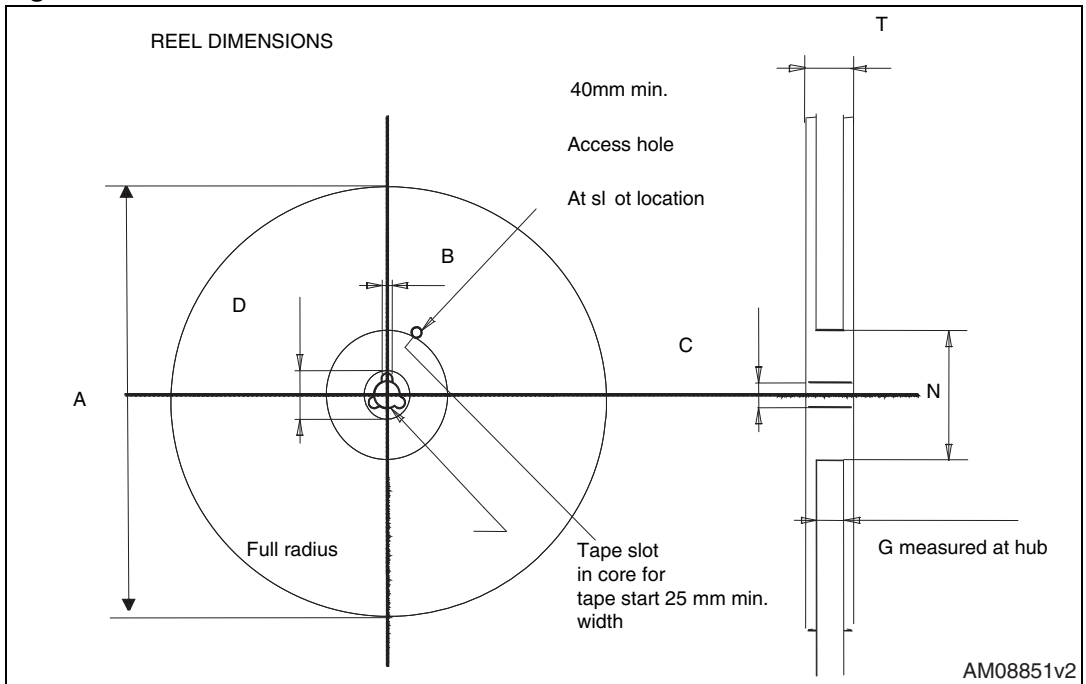


Figure 22. Reel



6 Revision history

Table 10. Document revision history

| Date | Revision | Changes |
|-------------|----------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| 23-May-2011 | 1 | First release. |
| 20-Jul-2012 | 2 | Document status promoted from preliminary data to datasheet. Updated mechanical data. Inserted Section 2.1: Electrical characteristics (curves) . Inserted Section 5: Packaging mechanical data . |

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